

GaAs pHEMT MMIC 1 WATT POWER AMPLIFIER, 40 - 43.5 GHz

Typical Applications

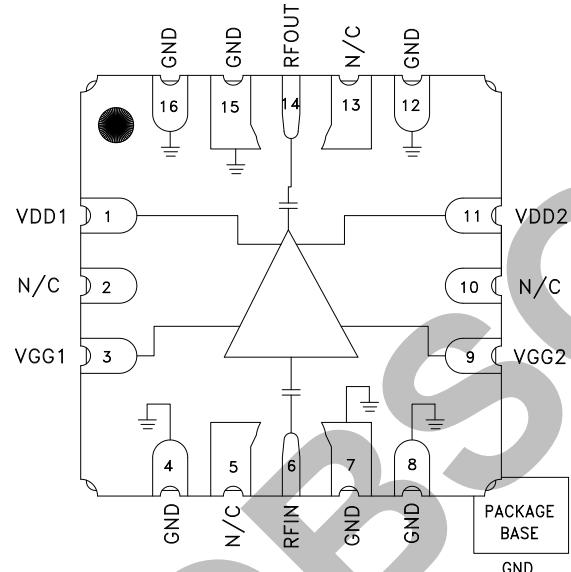
The HMC5929LS6 is ideal for:

- Point-to-Point Radios
- Point-to-Multi-Point Radios
- VSAT & SATCOM
- Military & Space

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AMPLIFIERS - LINEAR & POWER - SMT

Functional Diagram



Electrical Specifications

$T_A = +25^\circ C$, $Vdd = Vdd1 = Vdd2 = +6V$, $Idd = 900 \text{ mA}$ ^[1]

Parameter	Min.	Typ.	Max.	Units
Frequency Range		40 - 43.5		GHz
Gain	16	19		dB
Gain Variation Over Temperature		0.04		dB/°C
Input Return Loss		9		dB
Output Return Loss		12		dB
Output Power for 1 dB Compression (P1dB)	24.5	27		dBm
Saturated Output Power (Psat)		30		dBm
Output Third Order Intercept (IP3) ^[2]		36		dBm
Total Supply Current (Idd)		900		mA

[1] Adjust Vgg between -2 to 0V to achieve Idd = 900 mA typical.

[2] Measurement taken at +6V @ 900 mA, Pout / Tone = +18 dBm

Features

Saturated Output Power: +30 dBm @ 15% PAE
Output IP3: +36 dBm
High Gain: 19 dB
DC Supply: +6V @ 900 mA
No External Matching Required
16 Lead Ceramic 6x6 mm SMT Package: 36 mm²

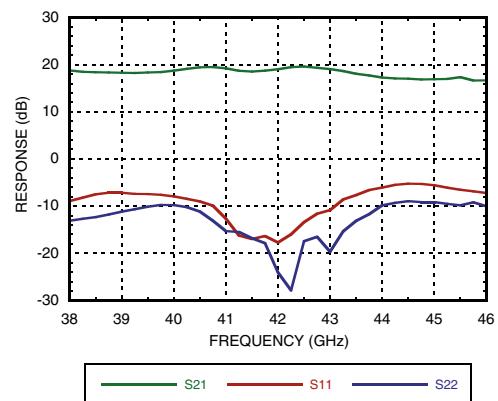
General Description

The HMC5929LS6 is a 4 stage GaAs pHEMT MMIC 1 Watt Power Amplifier which operates between 40 and 43.5 GHz. The amplifier provides 19 dB of gain, +30 dBm of saturated output power, and 15% PAE from a +6V supply. With an excellent IP3 of +36 dBm, the HMC5929LS6 is ideal for high linearity applications in military and space as well as point-to-point and point-to-multi-point radios. The HMC5929LS6 is housed in a ceramic air cavity package which exhibits low thermal resistance and is compatible with surface mount manufacturing techniques. The RF I/Os are internally matched and DC blocked for ease of integration into higher level assemblies.

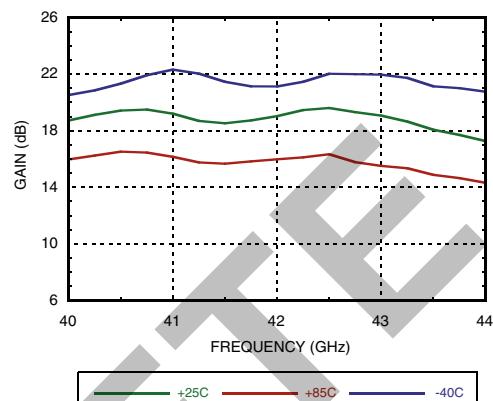
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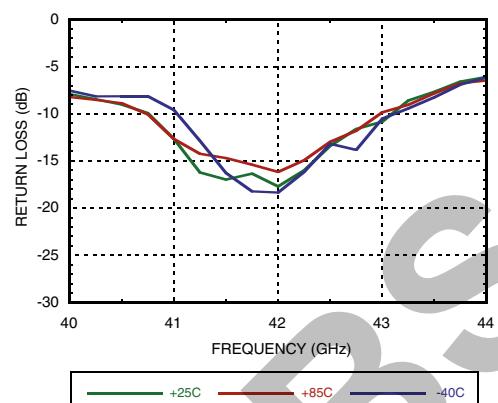
Broadband Gain & Return Loss vs. Frequency



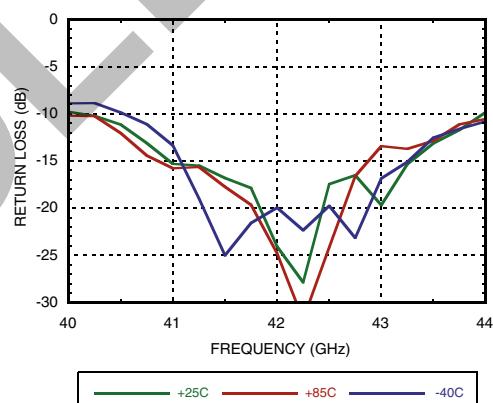
Gain vs. Temperature



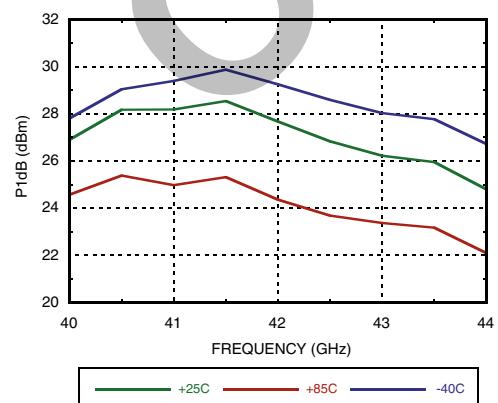
Input Return Loss vs. Temperature



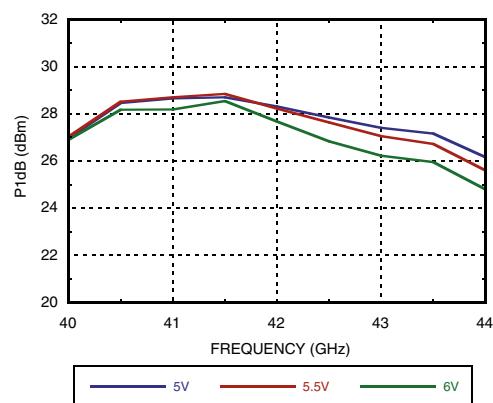
Output Return Loss vs. Temperature

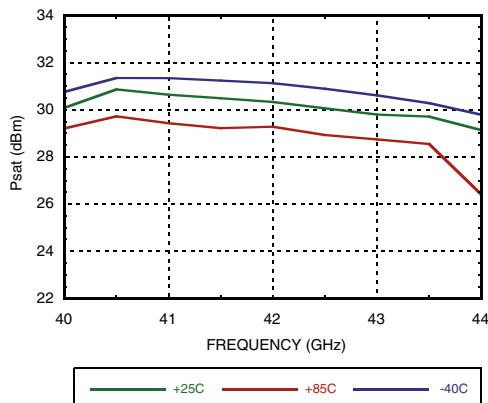
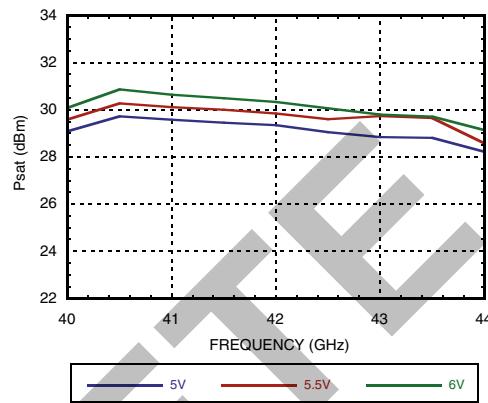
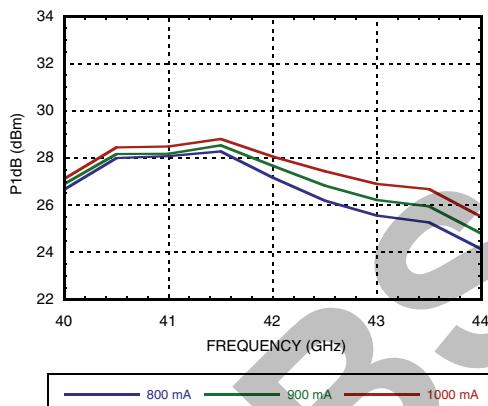
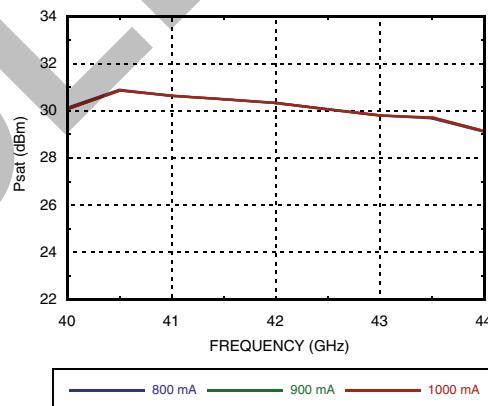
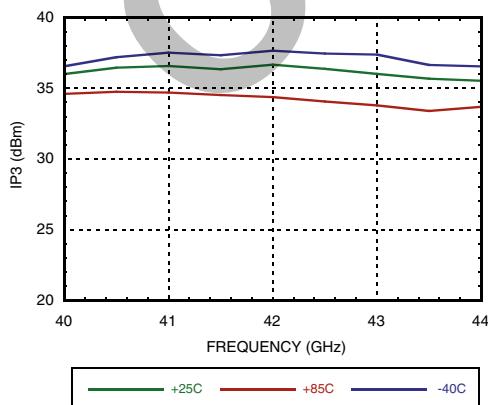
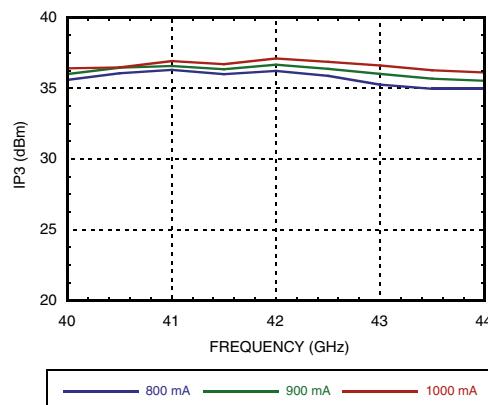


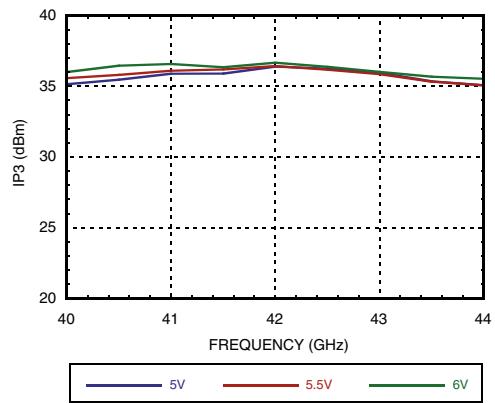
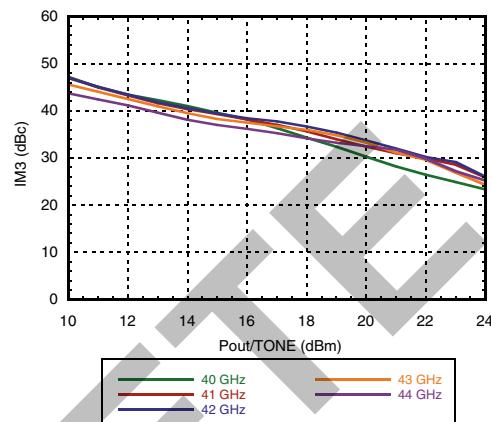
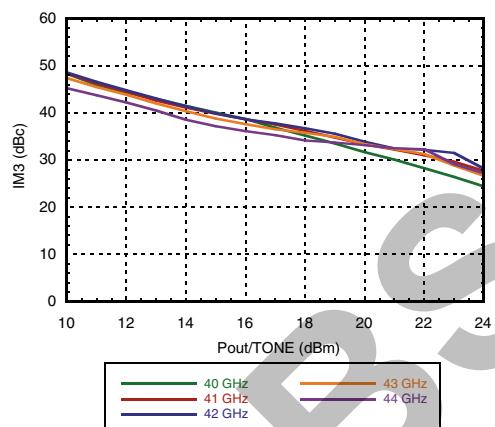
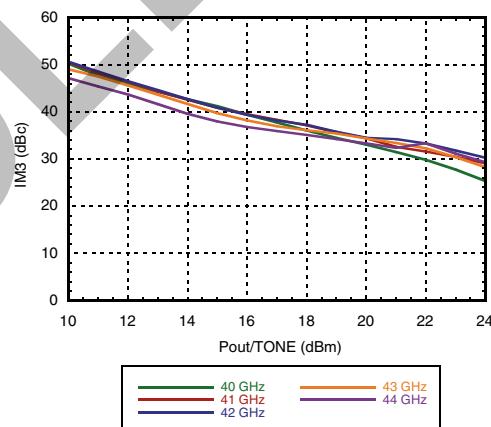
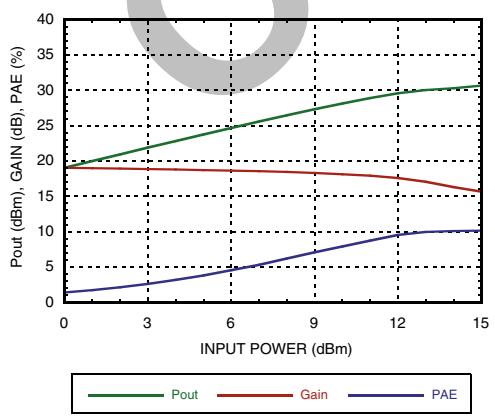
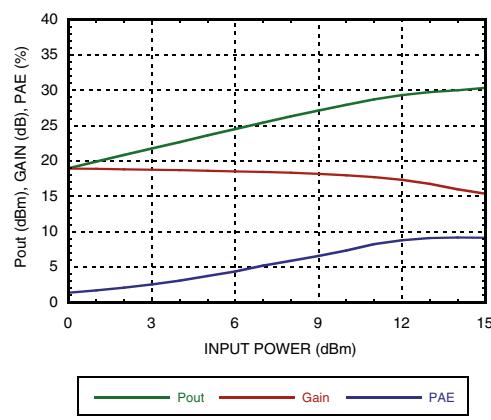
P1dB vs. Temperature

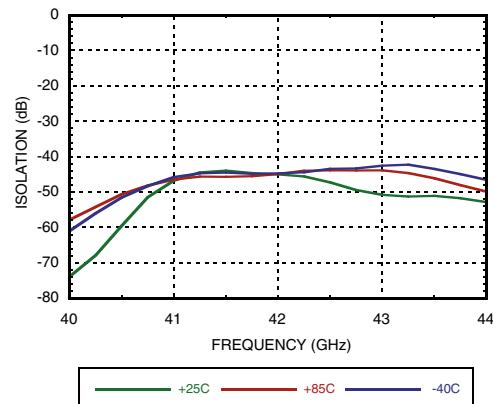
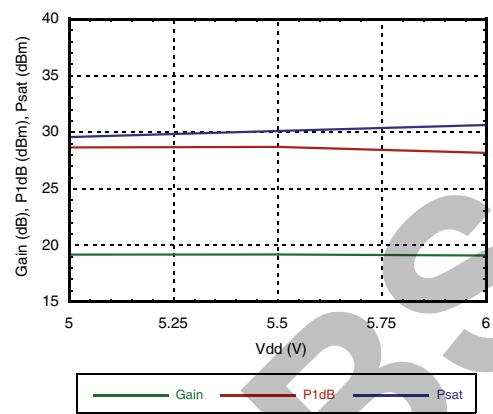


P1dB vs. Supply Voltage

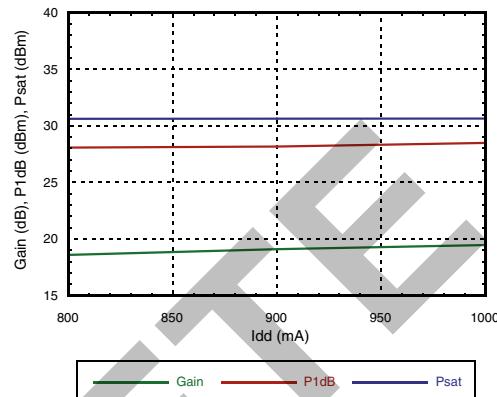
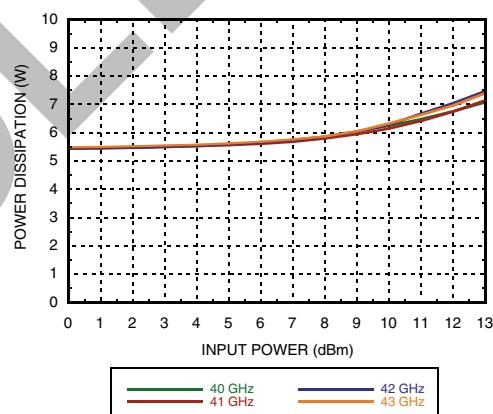


**GaAs pHEMT MMIC 1 WATT
POWER AMPLIFIER, 40 - 43.5 GHz**
Psat vs. Temperature

Psat vs. Supply Voltage

P1dB vs. Supply Current (Idd)

Psat vs. Supply Current (Idd)

***Output IP3 vs.
Temperature, Pout/Tone = +18 dBm***

***Output IP3 vs.
Supply Current, Pout/Tone = +18 dBm***


**GaAs pHEMT MMIC 1 WATT
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**Output IP3 vs.
Supply Voltage, Pout/Tone = +18 dBm**

Output IM3 @ Vdd = +5V

Output IM3 @ Vdd = +5.5V

Output IM3 @ Vdd = +6V

Power Compression @ 41 GHz

Power Compression @ 42 GHz


Reverse isolation vs. Temperature**Gain & Power vs.
Supply Voltage @ 41 GHz****Absolute Maximum Ratings**

Drain Bias Voltage (Vdd)	+7V
RF Input Power (RFIN)	+20 dBm
Channel Temperature	150 °C
Continuous Pdiss (T= 85 °C) (derate 95 mW/°C above 85 °C)	6.2 W
Thermal Resistance (channel to die bottom)	10.5 °C/W
Storage Temperature	-65 to +150 °C
Operating Temperature	-40 to +85 °C
ESD Sensitivity (HBM)	Class 1A

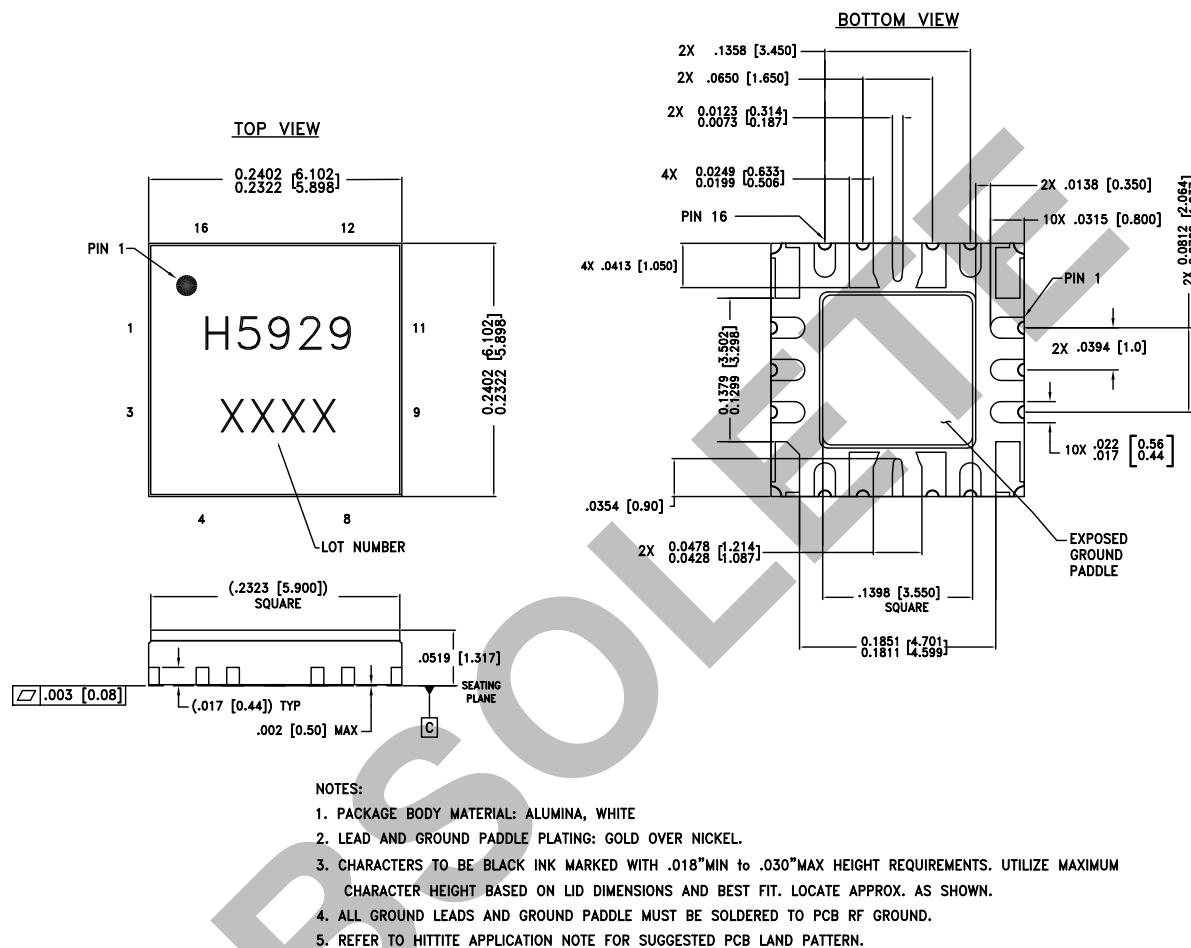
**GaAs pHEMT MMIC 1 WATT
POWER AMPLIFIER, 40 - 43.5 GHz****Gain & Power vs.
Supply Current @ 41 GHz****Power Dissipation****Typical Supply Current vs. Vdd**

Vdd (V)	Idd (mA)
+5.0	900
+5.5	900
+6.0	900

Note: Amplifier will operate over full voltage ranges shown above. Vgg adjusted to achieve Idd = 900 mA



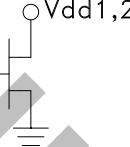
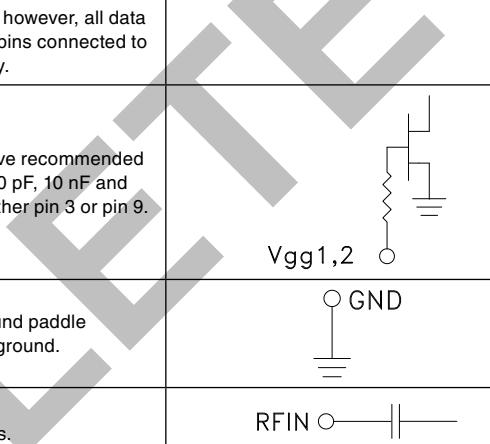
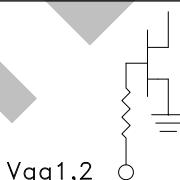
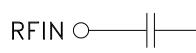
ELECTROSTATIC SENSITIVE DEVICE
OBSERVE HANDLING PRECAUTIONS

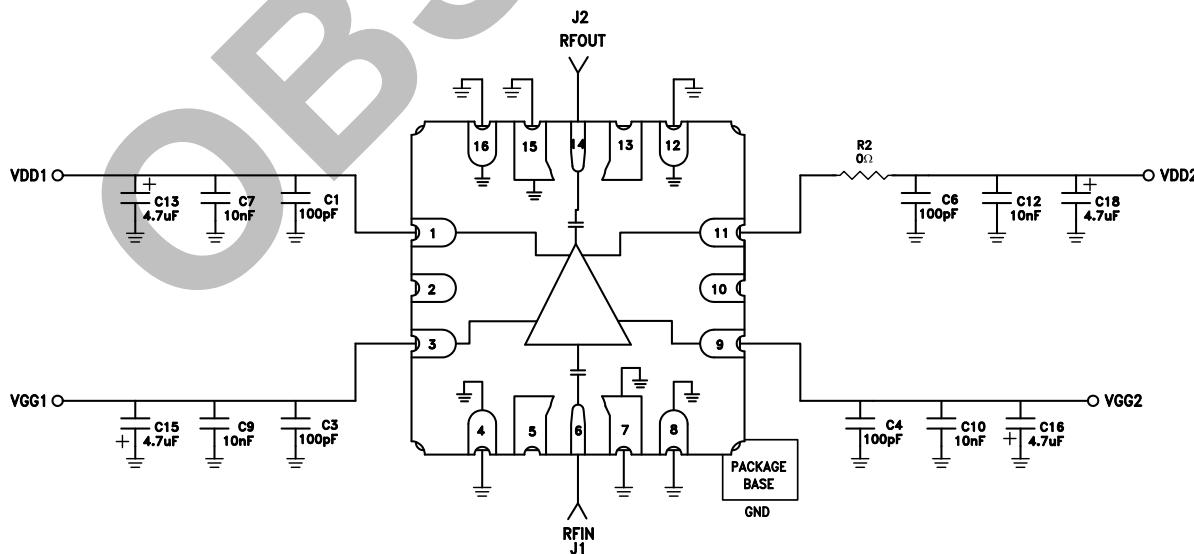
**GaAs pHEMT MMIC 1 WATT
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Outline Drawing

Table 1. Package Information

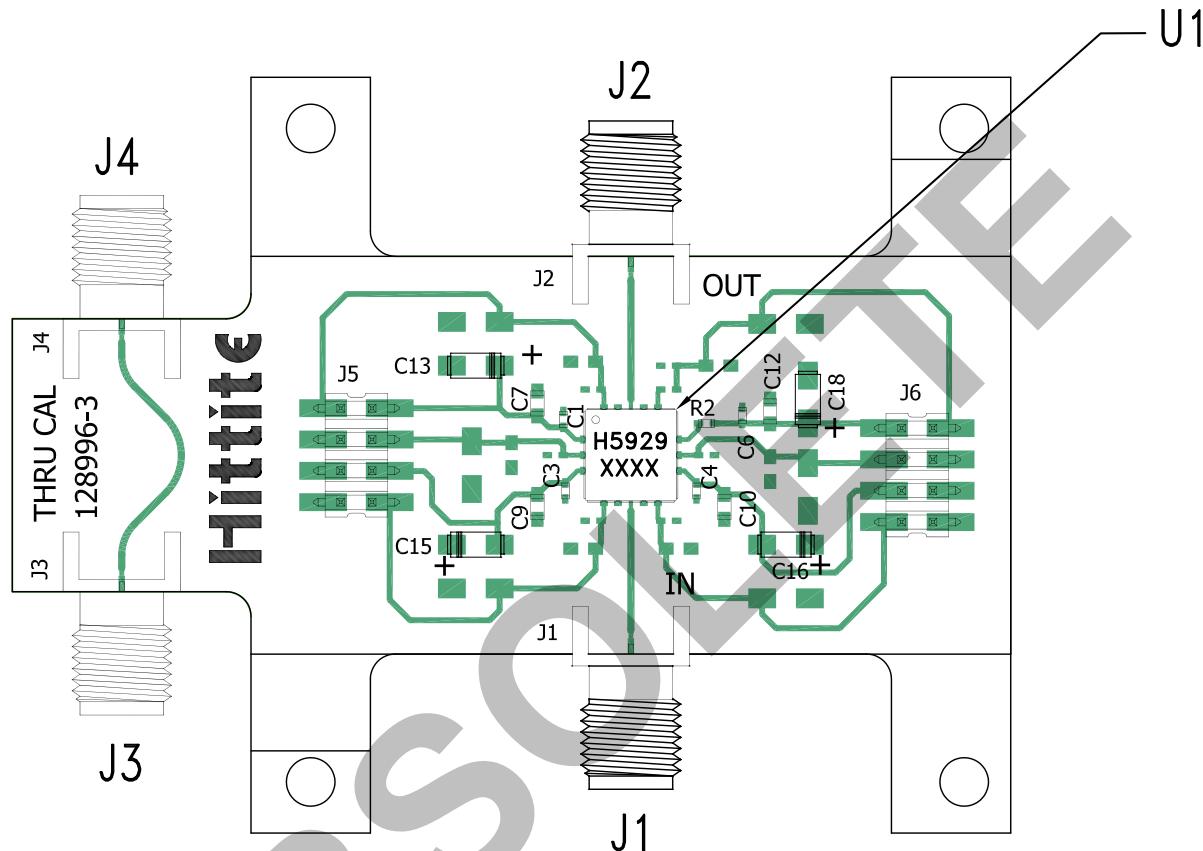
Part Number	Package Body Material	Lead Finish	MSL Rating	Package Marking ^[1]
HMC5929LS6	ALUMINA, WHITE	Gold over Nickel	N/A	H5929 XXXX

[1] 4-Digit lot number XXXX

**GaAs pHEMT MMIC 1 WATT
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Pin Descriptions

Pin Number	Function	Description	Interface Schematic
1, 11	Vdd1, Vdd2	Drain bias voltage. External bypass capacitors of 100 pF, 10 nF and 4.7 μ F are required for each pin.	
2, 5, 10, 13	N/C	These pins are not connected internally; however, all data shown herein was measured with these pins connected to RF/DC ground externally.	
3, 9	Vgg1, Vgg2	Gate control for PA. Adjust Vgg to achieve recommended bias current. External bypass caps 100 pF, 10 nF and 4.7 μ F are required. Apply Vgg bias to either pin 3 or pin 9.	
4, 7, 8, 12, 15, 16	GND	These pins and the exposed ground paddle must be connected to RF/DC ground.	
6	RFIN	This pin is AC coupled and matched to 50 Ohms.	
14	RFOUT	This pin is AC coupled and matched to 50 Ohms.	

Application Circuit


**GaAs pHEMT MMIC 1 WATT
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Evaluation PCB

List of Materials for Evaluation PCB EVAL01-HMC5929LS6^[1]

Item	Description
J1 - J4	"K" Connector, SRI
J5, J6	DC Pin
C1, C3, C4, C6	100 pF Capacitor, 0402 Pkg.
C7, C9, C10, C12	10000 pF Capacitor, 0603 Pkg.
C13, C15, C16, C18	4.7 uF Capacitor, Case A Pkg.
R2	0 Ohm Resistor, 0402 Pkg.
U1	HMC5929LS6 Amplifier
PCB [2]	128996 Eval Board

[1] Reference this number when ordering complete evaluation PCB

[2] Circuit Board Material: Rogers 4350

The circuit board used in the application should use RF circuit design techniques. Signal lines should have 50 Ohm impedance while the package ground leads and exposed paddle should be connected directly to the ground plane similar to that shown. A sufficient number of via holes should be used to connect the top and bottom ground planes. The evaluation board should be mounted to an appropriate heat sink. The evaluation circuit board shown is available from Hittite upon request.